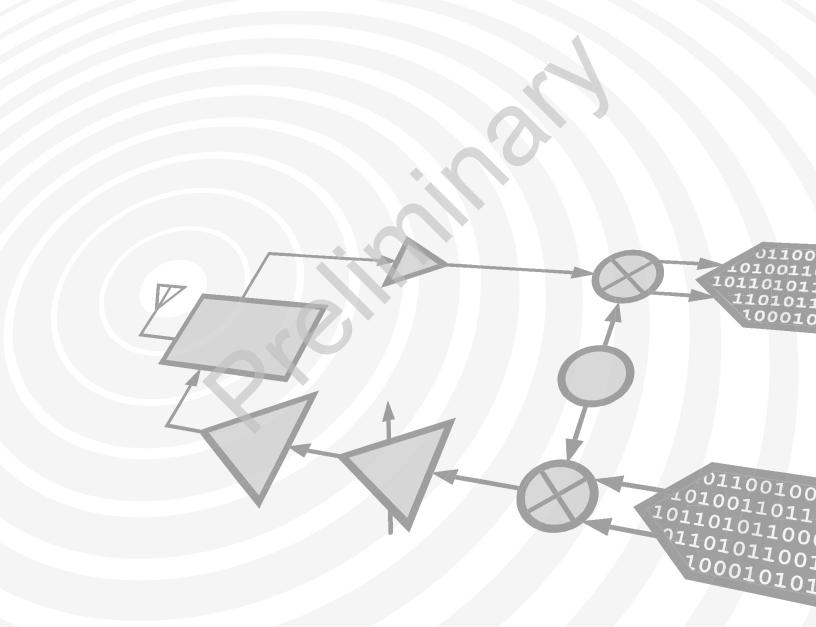




Analog Devices Welcomes Hittite Microwave Corporation



THIS PAGE INTENTIONALLY LEFT BLANK



v00.1115

GaAs MMIC I/Q MIXER 4 - 8.5 GHz

Typical Applications

The HMC525ALC4 is ideal for:

- Point-to-Point and Point-to-Multi-Point Radio
- VSAT

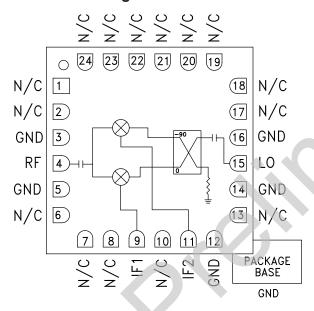
Features

Wide IF Bandwidth: DC - 3.5 GHz

Image Rejection: 40 dB LO to RF Isolation: 50 dB High Input IP3: +23 dBm

24 Lead 4x4mm SMT Package: 16mm²

Functional Diagram



General Description

The HMC525ALC4 is a compact I/Q MMIC mixer in a leadless "Pb free" RoHS compliant SMT package, which can be used as either an Image Reject Mixer or a Single Sideband Upconverter. The mixer utilizes two standard Hittite double balanced mixer cells and a 90 degree hybrid fabricated in a GaAs MESFET process. A low frequency quadrature hybrid was used to produce a 100 MHz USB IF output. This product is a much smaller alternative to hybrid style Image Reject Mixers and Sideband Upconverter assemblies. The HMC525ALC4 eliminates the need for wire allowing bonding use surface mount manufacturing techniques.

Electrical Specifications, $T_{\Delta} = +25$ °C, IF= 100 MHz, LO = +15 dBm*

Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Frequency Range, RF/LO	4.0 - 8.5 5			5.5 - 7.5	5.5 - 7.5		
Frequency Range, IF	DC - 3.5			DC - 3.5			GHz
Conversion Loss (As IRM)		8	11		7.5	9.5	dB
Image Rejection	20	35		30	40		dB
1 dB Compression (Input)		+14			+15		dBm
LO to RF Isolation	33	45		40	50		dB
LO to IF Isolation	14	20		17	20		dB
IP3 (Input)		+23			+23		dBm
Amplitude Balance		0.3			0.2		dB
Phase Balance		8			4		Deg

^{*} Unless otherwise noted, all measurements performed as downconverter.



v00.1115

GaAs MMIC I/Q MIXER 4 - 8.5 GHz

Harmonics of LO

LO Frag. (CLIE)	nLO Spur at RF Port					
LO Freq. (GHz)	1	2	3	4		
3.5	40	40	54	50		
4.5	43	45	58	53		
5.5	51	57	48	67		
6.5	59	63	64	56		
7.5	48	66	64	62		
8.5	44	65	60	67		
LO = +15 dBm						

Values in dBc below input LO level measured at RF Port.

Absolute Maximum Ratings

	_
RF / IF Input	+20 dBm
LO Drive	+27 dBm
Channel Temperature	150°C
Continuous Pdiss (T=85°C) (derate 9.7 mW/°C above 85°C)	631 mW
Thermal Resistance (R _{TH}) (junction to die bottom)	103 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-55 to +85 °C

MxN Spurious Outputs

	nLO						
mRF	0	1	2	3	4		
0	xx	-11	32	23	51		
1	32	0	42	51	66		
2	89	62	74	65	89		
3	89	89	89	82	89		
4	89	89	89	89	89		

RF = 5.6 GHz @ -10 dBm LO = 5.5 GHz @ +15 dBm

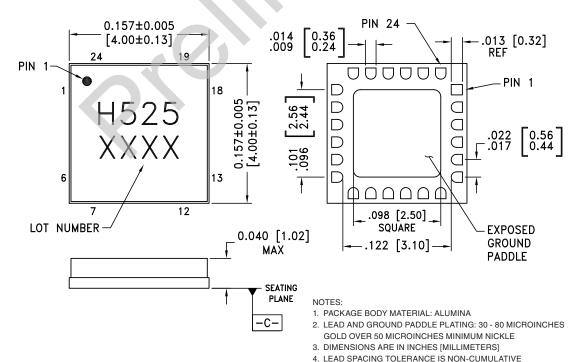
Data taken without IF hybrid

All values in dBc below IF power level



Outline Drawing

BOTTOM VIEW



5. PACKAGE WARP SHALL NOT EXCEED 0.05mm DATUM